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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	LCD, POR, PWM, Voltage Detect, WDT
Number of I/O	72
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	3.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2la88anfa-u0

Table 1.7 Specifications (2)

Item	Function		Specification		
Timer	Timer RB0, Timer RB1		8 bits × 2 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode		
	Timer RC		16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output: 3 pins), PWM2 mode (PWM output: 1 pin)		
	Timer RH		Real-time clock mode (counting of seconds, minutes, hours, day of the week, date, month, year), output compare mode		
	Timer RJ0 Timer RJ1 Timer RJ2	R8C/LA3A Group R8C/LA5A Group R8C/LA6A Group	Timer RJ0, Timer RJ1	16 bits × 2	Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
		R8C/LA8A Group	Timer RJ0, Timer RJ1, Timer RJ2	16 bits × 3	
Serial Interface	UART0		1 channel Clock synchronous serial I/O/UART		
	UART2		1 channel Clock synchronous serial I/O/UART, I ² C mode (I ² C-bus), multiprocessor communication function		
Synchronous Serial Communication Unit (SSU)			1 (shared with I ² C-bus)		
I ² C bus			1 (shared with SSU)		
A/D Converter		R8C/LA3A Group	10-bit resolution × 5 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
		R8C/LA5A Group	10-bit resolution × 7 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
		R8C/LA6A Group	10-bit resolution × 8 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
		R8C/LA8A Group	10-bit resolution × 12 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
Comparator B		R8C/LA3A Group	1 circuit (comparator B1)		
		R8C/LA5A Group R8C/LA6A Group R8C/LA8A Group	2 circuits (comparator B1, comparator B3)		

1.4 Pin Assignments

Figures 1.9 to 1.12 show pin assignments (top view). Tables 1.13 to 1.17 list the pin name information by pin number.

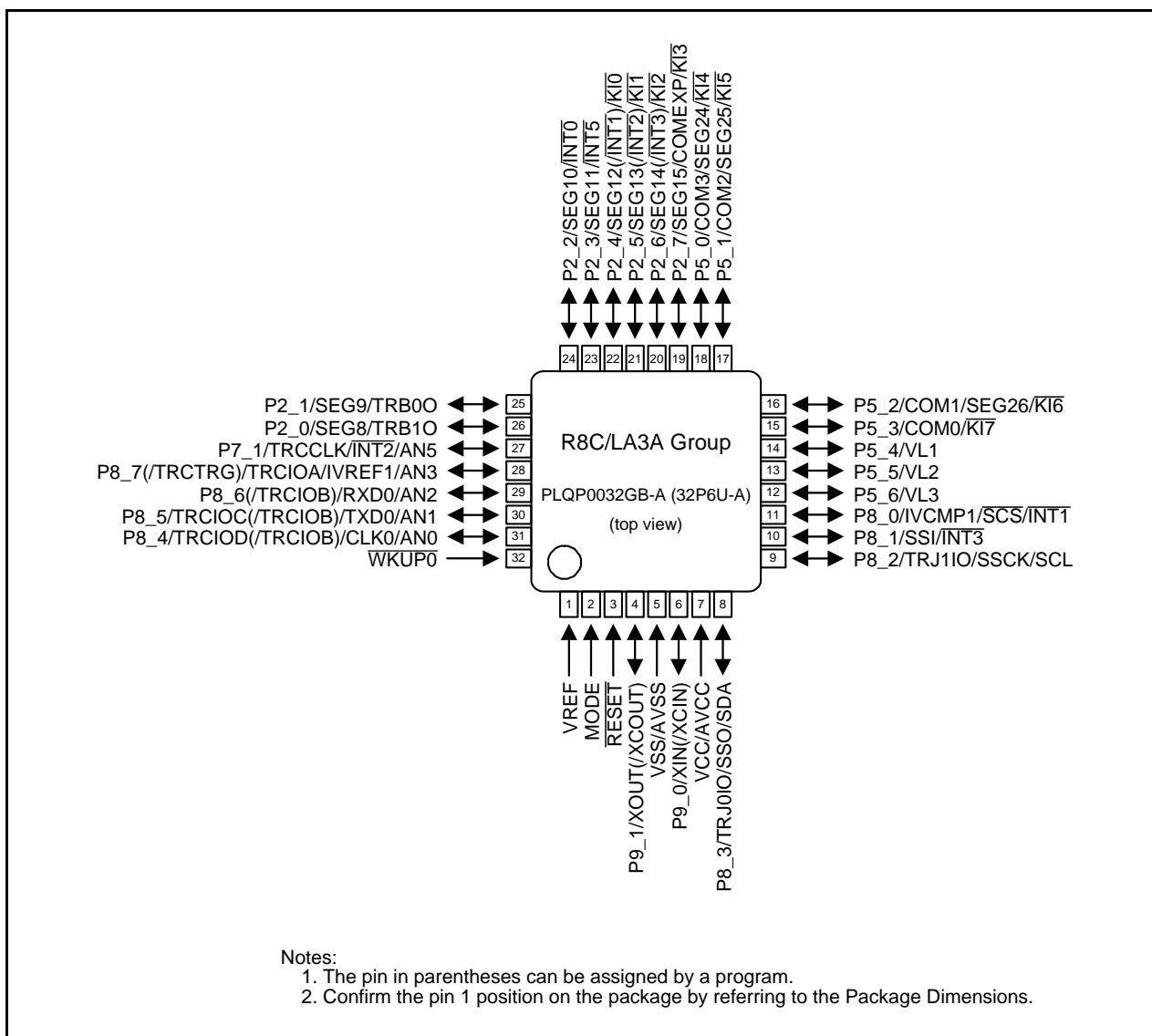


Figure 1.9 Pin Assignment (Top View) of PLQP0032GB-A Package

4. Special Function Registers (SFRs)

An SFR (special function register) is a control register for a peripheral function. Tables 4.1 to 4.9 list SFR information for R8C/LA5A Group, Tables 4.10 to 4.18 list SFR information for R8C/LA8A Group, and Table 4.19 lists the ID Code Areas and Option Function Select Area. The description offered in this chapter is based on the R8C/LA8A Group.

Table 4.1 SFR Information for R8C/LA5A Group (1) (1)

Address	Register	Symbol	After Reset
0000h			
0001h			
0002h			
0003h			
0004h	Processor Mode Register 0	PM0	00h
0005h	Processor Mode Register 1	PM1	00h 00000100b (2)
0006h	System Clock Control Register 0	CM0	00100000b
0007h	System Clock Control Register 1	CM1	00100000b
0008h	Module Standby Control Register 0	MSTCR0	00h
0009h	System Clock Control Register 3	CM3	00h
000Ah	Protect Register	PRCR	00h
000Bh	Reset Source Determination Register	RSTFR	XXh (3)
000Ch	Oscillation Stop Detection Register	OCD	00000100b (4) 00h (4)
000Dh	Watchdog Timer Reset Register	WDTR	XXh
000Eh	Watchdog Timer Start Register	WDTs	XXh
000Fh	Watchdog Timer Control Register	WDTC	00111111b
0010h	Module Standby Control Register 1	MSTCR1	00h
0011h			
0012h			
0013h			
0014h			
0015h			
0016h			
0017h			
0018h			
0019h			
001Ah			
001Bh			
001Ch	Count Source Protection Mode Register	CSPR	00h 10000000b (5)
001Dh			
001Eh			
001Fh			
0020h	Power-Off Mode Control Register 0	POMCR0	XXXXXX00b
0021h			
0022h			
0023h	High-Speed On-Chip Oscillator Control Register 0	FRA0	00h
0024h	High-Speed On-Chip Oscillator Frequency Control Register 0	FRC0	When shipping
0025h	High-Speed On-Chip Oscillator Control Register 2	FRA2	00h
0026h	On-Chip Reference Voltage Control Register	OCVREFCR	00h
0027h			
0028h			
0029h	High-Speed On-Chip Oscillator 18 MHz Set Value Register 0	FR18S0	XXh
002Ah	High-Speed On-Chip Oscillator 18 MHz Set Value Register 1	FR18S1	XXh
002Bh			
002Ch			
002Dh			
002Eh			
002Fh	High-Speed On-Chip Oscillator Frequency Control Register 1	FRC1	When shipping
0030h	Voltage Monitor Circuit Control Register	CMPA	00h
0031h	Voltage Monitor Circuit Edge Select Register	VCAC	00h
0032h			
0033h	Voltage Detect Register 1	VCA1	00001000b
0034h	Voltage Detect Register 2	VCA2	00h (6) 00100000b (7)
0035h			
0036h	Voltage Detection 1 Level Select Register	VD1LS	00000111b
0037h			
0038h	Voltage Monitor 0 Circuit Control Register	VW0C	1100X010b (6) 1100X011b (7)
0039h	Voltage Monitor 1 Circuit Control Register	VW1C	10001010b

X: Undefined

Notes:

- Blank spaces are reserved. No access is allowed.
- The CSPRO bit in the CSPR register is set to 1.
- The CWR bit in the RSTFR register is set to 0 after power-on, voltage monitor 0 reset, or exit from power-off 0 mode. Hardware reset, software reset, or watchdog timer reset does not affect this bit.
- The reset value differs depending on the mode.
- The CSPROINI bit in the OFS register is set to 0.
- The LVDAS bit in the OFS register is set to 1.
- The LVDAS bit in the OFS register is set to 0.

Table 4.16 SFR Information for R8C/LA8A Group (7) ⁽¹⁾

Address	Register	Symbol	After Reset
0180h	Timer RJ Pin Select Register	TRJSR	00h
0181h	Timer RB Pin Select Register	TRBSR	00h
0182h	Timer RC Pin Select Register 0	TRCPSR0	00h
0183h	Timer RC Pin Select Register 1	TRCPSR1	00h
0184h			
0185h			
0186h			
0187h			
0188h	UART0 Pin Select Register	U0SR	00h
0189h			
018Ah	UART2 Pin Select Register 0	U2SR0	00h
018Bh	UART2 Pin Select Register 1	U2SR1	00h
018Ch	SSU/IIC Pin Select Register	SSUIICSR	00h
018Dh	Timer RH Second Interrupt Control Register	TRHICR	X0XXXXXXb 00000001b ⁽³⁾
018Eh	INT Interrupt Input Pin Select Register	INTSR	00h
018Fh	I/O Function Pin Select Register	PINSR	00h
0190h			
0191h			
0192h			
0193h	SS Bit Counter Register	SSBR	11111000b
0194h	SS Transmit Data Register L / IIC bus Transmit Data Register ⁽²⁾	SSTDR/ICDRT	FFh
0195h	SS Transmit Data Register H ⁽²⁾	SSTDRH	FFh
0196h	SS Receive Data Register L / IIC bus Receive Data Register ⁽²⁾	SSRDR/ICDRR	FFh
0197h	SS Receive Data Register H ⁽²⁾	SSRDRH	FFh
0198h	SS Control Register H / IIC bus Control Register 1 ⁽²⁾	SSCRH/ICCR1	00h
0199h	SS Control Register L / IIC bus Control Register 2 ⁽²⁾	SSCRL/ICCR2	01111101b
019Ah	SS Mode Register / IIC bus Mode Register ⁽²⁾	SSMR/ICMR	00010000b/00011000b
019Bh	SS Enable Register / IIC bus Interrupt Enable Register ⁽²⁾	SSER/ICIER	00h
019Ch	SS Status Register / IIC bus Status Register ⁽²⁾	SSSR/ICSR	00h/0000X000b
019Dh	SS Mode Register 2 / Slave Address Register ⁽²⁾	SSMR2/SAR	00h
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h	Flash Memory Status Register	FST	10000X00b
01B3h			
01B4h	Flash Memory Control Register 0	FMR0	00h
01B5h	Flash Memory Control Register 1	FMR1	000000X0b
01B6h	Flash Memory Control Register 2	FMR2	00h
01B7h			
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

X: Undefined

Notes:

- Blank spaces are reserved. No access is allowed.
- Selectable by the IICSEL bit in the SSUIICSR register.
- This is the reset value after reset by RTCRST bit in TRHCR register.

5. Electrical Characteristics

5.1 Electrical Characteristics (R8C/LA3A Group and R8C/LA5A Group)

5.1.1 Absolute Maximum Ratings

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V _{cc} /AV _{cc}	Supply voltage			−0.3 to 6.5	V
V _i	Input voltage	XIN	XIN-XOUT oscillation on (oscillation buffer ON) ⁽¹⁾	−0.3 to 1.9	V
		XIN	XIN-XOUT oscillation on (oscillation buffer OFF) ⁽¹⁾	−0.3 to V _{cc} + 0.3	V
		P5_4/VL1		−0.3 to VL2 ⁽²⁾	V
		P5_5/VL2		VL1 to VL3	V
		P5_6/VL3		VL2 to 6.5	V
		Other pins		−0.3 to V _{cc} + 0.3	V
V _o	Output voltage	XOUT	XIN-XOUT oscillation on (oscillation buffer ON) ⁽¹⁾	−0.3 to 1.9	V
		XOUT	XIN-XOUT oscillation on (oscillation buffer OFF) ⁽¹⁾	−0.3 to V _{cc} + 0.3	V
		COM0 to COM3		−0.3 to VL3	V
		SEG0 to SEG26		−0.3 to VL3	V
		Other pins		−0.3 to V _{cc} + 0.3	V
P _d	Power dissipation		−40 °C ≤ T _{opr} ≤ 85 °C	500	mW
T _{opr}	Operating ambient temperature			−20 to 85 (N version)/ −40 to 85 (D version)	°C
T _{stg}	Storage temperature			−65 to 150	°C

Notes:

- For the register settings for each operation, refer to **7. I/O Ports** and **9. Clock Generation Circuit** in the User's Manual: Hardware.
- The VL1 voltage should be VCC or below.

5.1.3 Peripheral Function Characteristics

Table 5.3 A/D Converter Characteristics
($V_{CC}/AV_{CC} = V_{ref} = 1.8$ to 5.5 V, $V_{SS} = 0$ V, and $T_{opr} = -20$ to 85 °C (N version)/
 -40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
—	Resolution		Vref = AVCC		—	—	10	Bit
—	Absolute accuracy (2)	10-bit mode	Vref = AVCC = 5.0 V	AN0 to AN6 input	—	—	±3	LSB
			Vref = AVCC = 2.2 V	AN0 to AN6 input	—	—	±5	LSB
			Vref = AVCC = 1.8 V	AN0 to AN6 input	—	—	±5	LSB
		8-bit mode	Vref = AVCC = 5.0 V	AN0 to AN6 input	—	—	±2	LSB
			Vref = AVCC = 2.2 V	AN0 to AN6 input	—	—	±2	LSB
			Vref = AVCC = 1.8 V	AN0 to AN6 input	—	—	±2	LSB
φAD	A/D conversion clock		4.0 ≤ Vref = AVCC ≤ 5.5 V (1)		1	—	20	MHz
			3.2 ≤ Vref = AVCC ≤ 5.5 V (1)		1	—	16	MHz
			2.7 ≤ Vref = AVCC ≤ 5.5 V (1)		1	—	10	MHz
			1.8 ≤ Vref = AVCC ≤ 5.5 V (1)		1	—	8	MHz
—	Tolerance level impedance				—	3	—	kΩ
tCONV	Conversion time	10-bit mode	Vref = AVCC = 5.0 V, φAD = 20 MHz		2.2	—	—	μs
		8-bit mode	Vref = AVCC = 5.0 V, φAD = 20 MHz		2.2	—	—	ms
tsAMP	Sampling time		φAD = 20 MHz		0.8	—	—	μs
IVref	Vref current		VCC = 5 V, XIN = f1 = φAD = 20 MHz		—	45	—	μA
Vref	Reference voltage				1.8	—	AVCC	V
VIA	Analog input voltage (3)				0	—	Vref	V
OCVREF	On-chip reference voltage		2 MHz ≤ φAD ≤ 4 MHz		1.53	1.70	1.87	V

Notes:

1. The A/D conversion result will be undefined in wait mode, stop mode, power-off mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
2. This applies when the peripheral functions are stopped.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.4 Temperature Sensor Characteristics
($V_{SS} = 0$ V and $T_{opr} = -20$ to 85 °C (N version)/ -40 to 85 °C (D version), unless
otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
V_{TMP}	Temperature sensor output voltage	$1.8 \text{ V} \leq V_{ref} = AV_{CC} \leq 5.5 \text{ V}$ $\phi AD = 1.0 \text{ MHz to } 5.0 \text{ MHz}$ Ambient temperature = 25 °C	550	600	650	mV
—	Temperature coefficient	$1.8 \text{ V} \leq V_{ref} = AV_{CC} \leq 5.5 \text{ V}$ $\phi AD = 1.0 \text{ MHz to } 5.0 \text{ MHz}$ Ambient temperature = 25 °C	—	-2.1	—	mV/°C
—	Start-up time	$1.8 \text{ V} \leq V_{ref} = AV_{CC} \leq 5.5 \text{ V}$ $\phi AD = 1.0 \text{ MHz to } 5.0 \text{ MHz}$	—	—	200	μs
I_{TMP}	Operating current	$1.8 \text{ V} \leq V_{ref} = AV_{CC} \leq 5.5 \text{ V}$ $\phi AD = 1.0 \text{ MHz to } 5.0 \text{ MHz}$	—	100	—	μA

Table 5.7 Flash Memory (Program ROM) Characteristics
(VCC = 1.8 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽¹⁾		10,000 ⁽²⁾	—	—	times
—	Byte program time		—	80	—	μs
—	Block erase time		—	0.12	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	0.25 + CPU clock × 3 cycles	ms
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		—	—	30 + CPU clock × 1 cycle	μs
—	Program, erase voltage		1.8	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time ⁽⁶⁾	Ambient temperature = 85 °C	10	—	—	year

Notes:

- Definition of programming/erasure endurance
 The programming and erasure endurance is defined on a per-block basis.
 If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
 However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
- Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
- In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
- If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
- Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
- The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.11 Voltage Detection 2 Circuit Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V _{det2}	Voltage detection level V _{det2_0} ⁽¹⁾	At the falling of V _{CC}	3.70	4.0	4.30	V
–	Hysteresis width at the rising of V _{CC} in voltage detection 2 circuit		–	0.10	–	V
–	Voltage detection 2 circuit response time ⁽²⁾	In operation		20	150	μs
		In stop mode		200	500	μs
–	Voltage detection circuit self power consumption	VCA27 = 1, V _{CC} = 5.0 V	–	1.7	–	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽³⁾		–	–	100	μs

Notes:

1. The voltage detection level varies with detection targets. Select the level with the VCA24 bit in the VCA2 register.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.12 Power-on Reset Circuit Characteristics ⁽¹⁾
(T_{opr} = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _{trh}	External power V _{CC} rise gradient		0	–	50000	mV/ms

Note:

1. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.

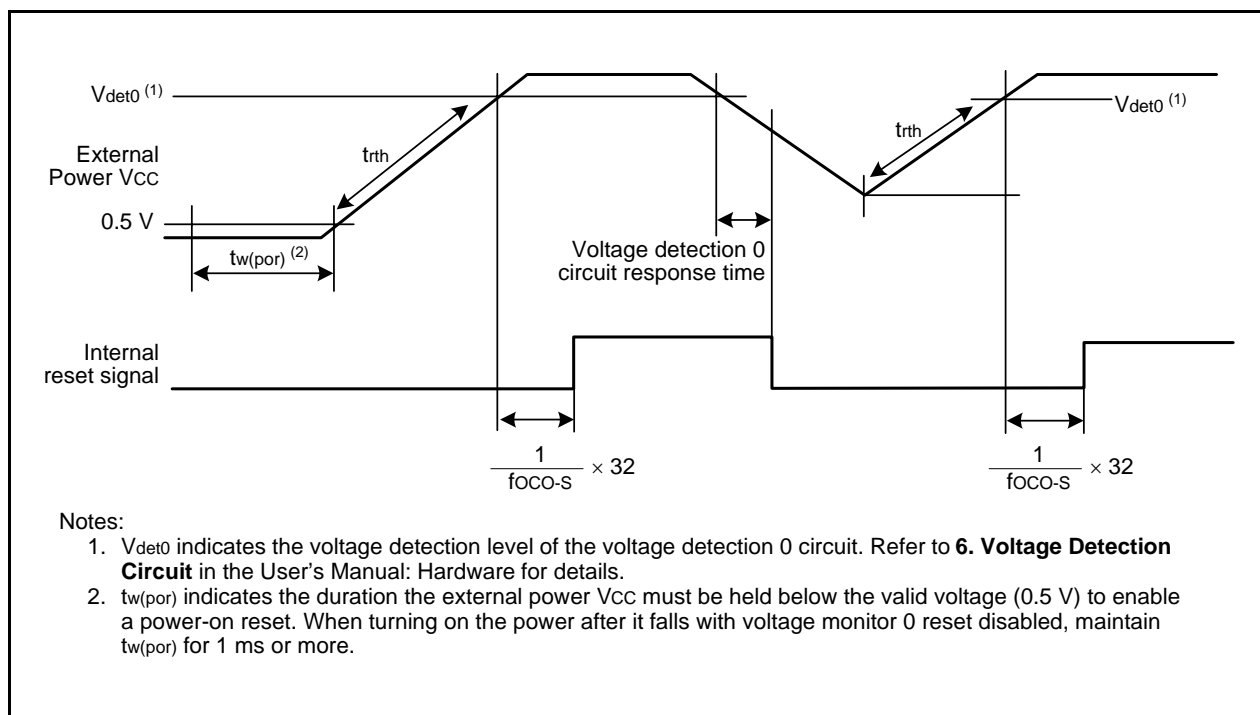


Figure 5.3 Power-on Reset Circuit Characteristics

Table 5.13 High-speed On-Chip Oscillator Circuit Characteristics
($V_{CC} = 1.8$ to 5.5 V and $T_{opr} = -20$ to 85 °C (N version)/ -40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	$V_{CC} = 1.8$ V to 5.5 V -20 °C $\leq T_{opr} \leq 85$ °C	19.2	20	20.8	MHz
		$V_{CC} = 1.8$ V to 5.5 V -40 °C $\leq T_{opr} \leq 85$ °C	19.0	20	21.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register ⁽¹⁾	$V_{CC} = 1.8$ V to 5.5 V -20 °C $\leq T_{opr} \leq 85$ °C	17.694	18.432	19.169	MHz
		$V_{CC} = 1.8$ V to 5.5 V -40 °C $\leq T_{opr} \leq 85$ °C	17.510	18.432	19.353	MHz
—	Oscillation stability time		—	5	30	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0$ V, $T_{opr} = 25$ °C	—	530	—	μA

Note:

1. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.14 Low-speed On-Chip Oscillator Circuit Characteristics
($V_{CC} = 1.8$ to 5.5 V and $T_{opr} = -20$ to 85 °C (N version)/ -40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time		—	—	35	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0$ V, $T_{opr} = 25$ °C	—	2	—	μA
fOCO-WDT	Low-speed on-chip oscillator frequency for the watchdog timer		60	125	250	kHz
—	Oscillation stability time		—	—	35	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0$ V, $T_{opr} = 25$ °C	—	2	—	μA

Table 5.15 Power Supply Circuit Characteristics
($V_{CC} = 1.8$ to 5.5 V, $V_{SS} = 0$ V, and $T_{opr} = 25$ °C, unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _d (P-R)	Time for internal power supply stabilization during power-on ⁽¹⁾		—	—	2000	μs

Note:

1. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.16 LCD Drive Control Circuit Characteristics
(V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/
–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
VLCD	LCD power supply voltage	VLCD = VL3	2.2	–	5.5	V
VL2	VL2 voltage		VL1	–	VL3	V
VL1	VL1 voltage		1	–	VL2 (2)	V
f(FR)	Frame frequency		50	–	180	Hz
ILCD	LCD drive control circuit current		–	(1)	–	μA

Notes:

1. Refer to Table 5.19 DC Characteristics (2), Table 5.21 DC Characteristics (4), and Table 5.23 DC Characteristics (6).
2. The VL1 voltage should be VCC or below.

Table 5.17 Power-Off Mode Characteristics
(V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/
–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	Power-off mode operating supply voltage		1.8	–	5.5	V

Table 5.21 DC Characteristics (4) [2.7 V ≤ V_{CC} < 4.0 V]**(T_{opr} = −20 to 85 °C (N version)/ −40 to 85 °C (D version), unless otherwise specified.)**

Symbol	Parameter		Condition							Standard			Unit
			Oscillation Circuit		On-Chip Oscillator		CPU Clock	Low-Power-Consumption Setting	Other	Min.	Typ. (3)	Max .	
			XIN (2)	XCIN	High-Speed	Low-Speed							
Icc	Power supply current (1)	High-speed clock mode	20 MHz	Off	Off	125 kHz	No division	—		—	4.7	10	mA
			10 MHz	Off	Off	125 kHz	No division	—		—	2.3	6	mA
			20 MHz	Off	Off	Off	No division	FMR27 = 1 MSTCR0 = BEh MSTCR1 = 3Fh	Flash memory off Program operation on RAM Module standby setting enabled	—	2.9	—	mA
			20 MHz	Off	Off	125 kHz	Divide-by-8	—		—	1.8	—	mA
			10 MHz	Off	Off	125 kHz	Divide-by-8	—		—	1.0	—	mA
		High-speed on-chip oscillator mode	Off	Off	20 MHz	125 kHz	No division	—		—	5.0	11	mA
			Off	Off	20 MHz	125 kHz	Divide-by-8	—		—	2.1	—	mA
			Off	Off	10 MHz	125 kHz	No division	—		—	2.9	—	mA
			Off	Off	10 MHz	125 kHz	Divide-by-8	—		—	1.5	—	mA
			Off	Off	4 MHz	125 kHz	Divide-by-16	MSTCR0 = BEh MSTCR1 = 3Fh		—	0.9	—	mA
		Low-speed on-chip oscillator mode	Off	Off	Off	125 kHz	No division	FMR27 = 1 VCA20 = 0		—	106	300	μA
			Off	Off	Off	125 kHz	Divide-by-8	FMR27 = 1 VCA20 = 0		—	54	200	μA
		Low-speed clock mode	Off	32 kHz	Off	Off	No division	FMR27 = 1 VCA20 = 0		—	54	200	μA
			Off	32 kHz	Off	Off	No division	FMSTP = 1 VCA20 = 0	Flash memory off Program operation on RAM	—	36	—	μA
		Wait mode	Off	Off	Off	125 kHz	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1	While a WAIT instruction is executed Peripheral clock operation	—	9.0	50	μA
			Off	Off	Off	125 kHz	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off	—	2.5	31	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 0	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode LCD drive control circuit (4) When external division resistors are used	—	3.1	—	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	—	1.7	—	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 0 Topr = 25 °C Peripheral clock off	—	0.5	2.2	μA
		Stop mode	Off	Off	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 0 Topr = 85 °C Peripheral clock off	—	1.2	—	μA
			Off	Off	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 0 Topr = 25 °C	—	0.01	0.1	μA
		Power-off mode	Off	Off	Off	Off	—	—	Power-off 0 Topr = 85 °C	—	0.02	—	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 25 °C	—	1.3	4.5	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85 °C	—	2.2	—	μA
Off	32 kHz		Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85 °C	—	2.2	—	μA		

Notes:

- V_{CC} = 2.7 V to 4.0 V, single chip mode, output pins are open, and other pins are V_{SS}.
- XIN is set to square wave input.
- V_{CC} = 3.0 V
- VLCD = V_{CC}, external division resistors are used for VL3 to VL1, 1/3 bias, 1/4 duty, f(FR) = 64 Hz, SEG0 to SEG26 are selected, and segment and common output pins are open. The standard value does not include the current that flows through external division resistors.

5.1.5 AC Characteristics

Table 5.24 Timing Requirements of Synchronous Serial Communication Unit (SSU)
(V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/
–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
tsucyc	SSCK clock cycle time			4	–	–	tcyc (1)
tHI	SSCK clock “H” width			0.4	–	0.6	tsucyc
tLO	SSCK clock “L” width			0.4	–	0.6	tsucyc
tRISE	SSCK clock rising time	Master		–	–	1	tcyc (1)
		Slave		–	–	1	μs
tFALL	SSCK clock falling time	Master		–	–	1	tcyc (1)
		Slave		–	–	1	μs
tsu	SSO, SSI data input setup time			100	–	–	ns
tH	SSO, SSI data input hold time			1	–	–	tcyc (1)
tLEAD	$\overline{\text{SCS}}$ setup time	Slave		1tcyc + 50	–	–	ns
tLAG	$\overline{\text{SCS}}$ hold time	Slave		1tcyc + 50	–	–	ns
tOD	SSO, SSI data output delay time			–	–	1tcyc + 20	ns
tsa	SSI slave access time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5tcyc + 100	ns
			1.8 V ≤ V _{CC} < 2.7 V	–	–	1.5tcyc + 200	ns
tor	SSI slave out open time		2.7 V ≤ V _{CC} ≤ 5.5 V	–	–	1.5tcyc + 100	ns
			1.8 V ≤ V _{CC} < 2.7 V	–	–	1.5tcyc + 200	ns

Note:

1. 1tcyc = 1/f1(s)

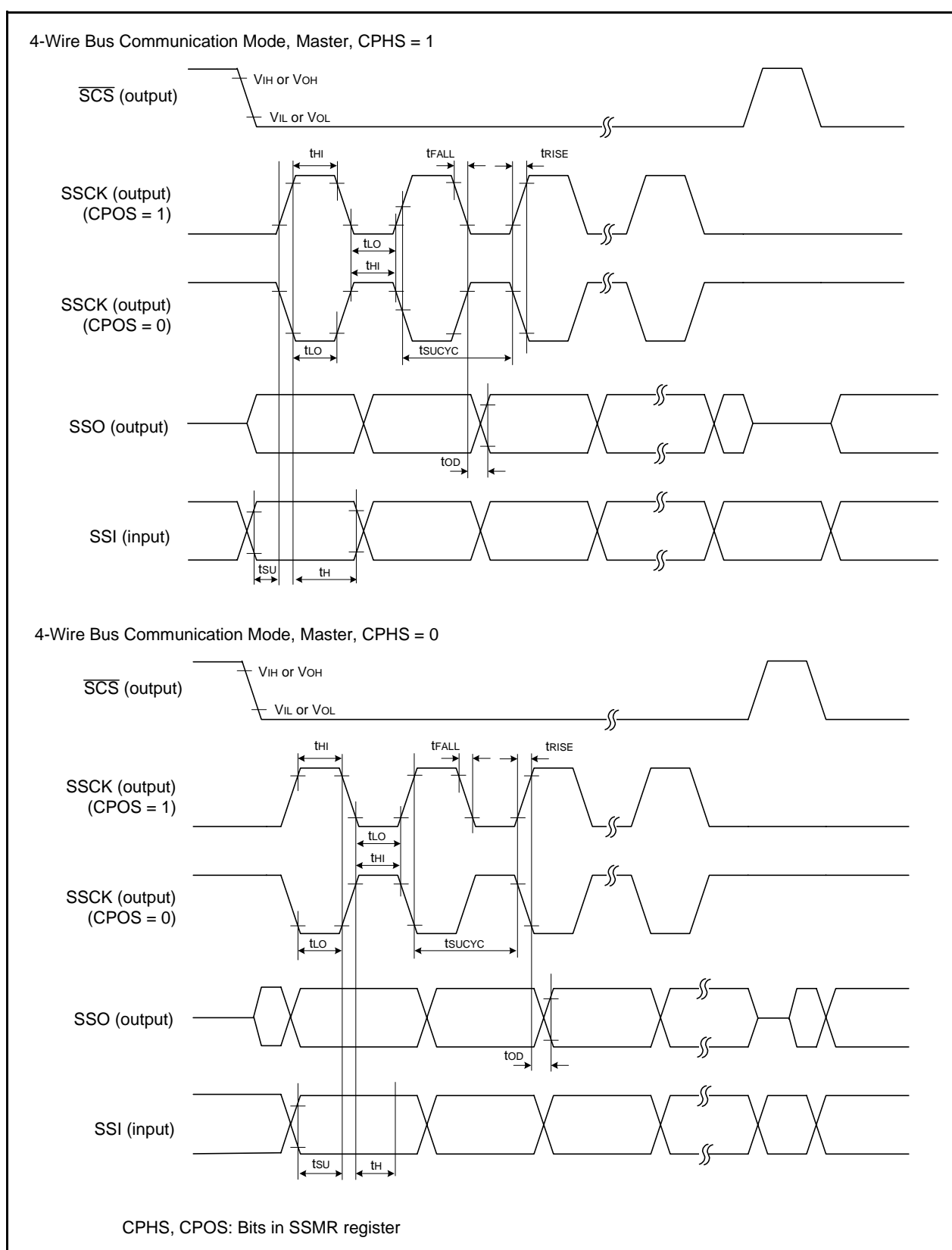


Figure 5.4 I/O Timing of Synchronous Serial Communication Unit (SSU) (Master)

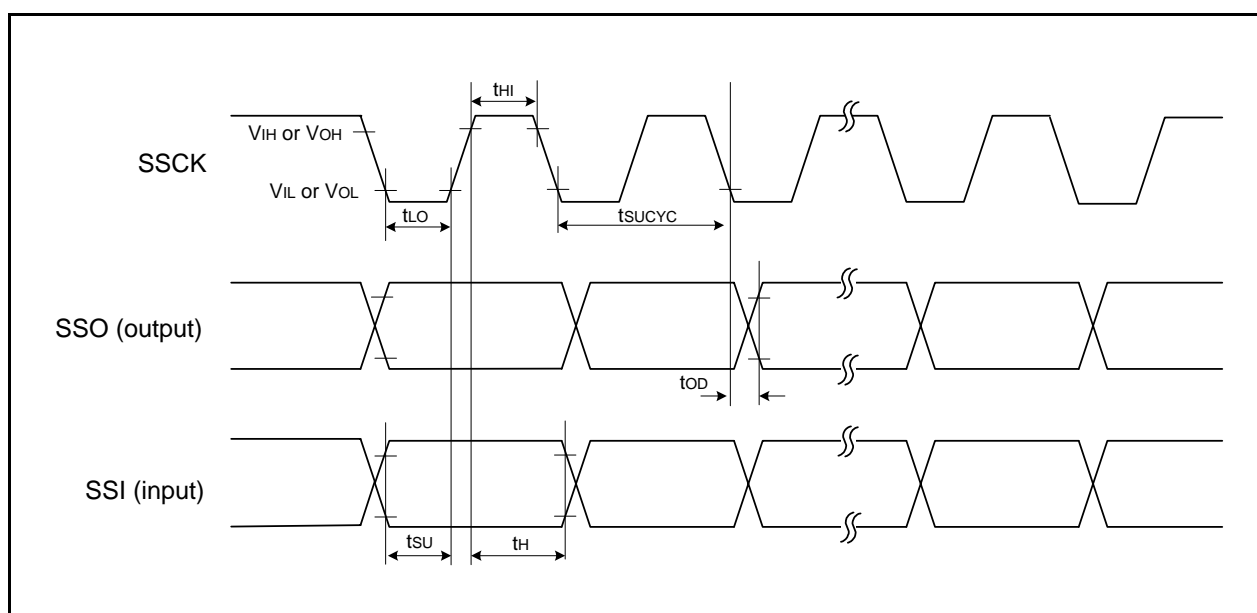


Figure 5.6 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

5.2 Electrical Characteristics (R8C/LA6A Group and R8C/LA8A Group)

5.2.1 Absolute Maximum Ratings

Table 5.30 Absolute Maximum Ratings

Symbol	Parameter		Condition	Rated Value	Unit
V _{CC} /AV _{CC}	Supply voltage			–0.3 to 6.5	V
V _I	Input voltage	XIN	XIN-XOUT oscillation on (oscillation buffer ON) ⁽¹⁾	–0.3 to 1.9	V
		XIN	XIN-XOUT oscillation on (oscillation buffer OFF) ⁽¹⁾	–0.3 to V _{CC} + 0.3	V
		P5_4/VL1		–0.3 to VL2 ⁽²⁾	V
		P5_5/VL2		VL1 to VL3	V
		P5_6/VL3		VL2 to 6.5	V
		Other pins		–0.3 to V _{CC} + 0.3	V
V _O	Output voltage	XOUT	XIN-XOUT oscillation on (oscillation buffer ON) ⁽¹⁾	–0.3 to 1.9	V
		XOUT	XIN-XOUT oscillation on (oscillation buffer OFF) ⁽¹⁾	–0.3 to V _{CC} + 0.3	V
		COM0 to COM3		–0.3 to VL3	V
		SEG0 to SEG39		–0.3 to VL3	V
		Other pins		–0.3 to V _{CC} + 0.3	V
P _d	Power dissipation		–40°C ≤ T _{opr} ≤ 85°C	500	mW
T _{opr}	Operating ambient temperature			–20 to 85 (N version)/ –40 to 85 (D version)	°C
T _{stg}	Storage temperature			–65 to 150	°C

Notes:

1. For the register settings for each operation, refer to **7. I/O Ports** and **9. Clock Generation Circuit** in the User's Manual: Hardware.
2. The VL1 voltage should be V_{CC} or below.

5.2.2 Recommended Operating Conditions

Table 5.31 Recommended Operating Conditions
(VCC = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
V _{CC} /AV _{CC}	Supply voltage					1.8	–	5.5	V
V _{SS} /AV _{SS}	Supply voltage					–	0	–	V
V _{IH}	Input “H” voltage	Other than CMOS input			4.0 V ≤ V _{CC} ≤ 5.5 V	0.8 V _{CC}	–	V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0.8 V _{CC}	–	V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0.9 V _{CC}	–	V _{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection : 0.35 V _{CC}	4.0 V ≤ V _{CC} ≤ 5.5 V	0.5 V _{CC}	–	V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0.55 V _{CC}	–	V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0.65 V _{CC}	–	V _{CC}	V
				Input level selection : 0.5 V _{CC}	4.0 V ≤ V _{CC} ≤ 5.5 V	0.65 V _{CC}	–	V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0.7 V _{CC}	–	V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0.8 V _{CC}	–	V _{CC}	V
				Input level selection : 0.7 V _{CC}	4.0 V ≤ V _{CC} ≤ 5.5 V	0.85 V _{CC}	–	V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0.85 V _{CC}	–	V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0.85 V _{CC}	–	V _{CC}	V
V _{IL}	Input “L” voltage	Other than CMOS input			4.0 V ≤ V _{CC} ≤ 5.5 V	0	–	0.2 V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0	–	0.2 V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0	–	0.05 V _{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection : 0.35 V _{CC}	4.0 V ≤ V _{CC} ≤ 5.5 V	0	–	0.2 V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0	–	0.2 V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0	–	0.2 V _{CC}	V
				Input level selection : 0.5 V _{CC}	4.0 V ≤ V _{CC} ≤ 5.5 V	0	–	0.4 V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0	–	0.3 V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0	–	0.2 V _{CC}	V
				Input level selection : 0.7 V _{CC}	4.0 V ≤ V _{CC} ≤ 5.5 V	0	–	0.55 V _{CC}	V
					2.7 V ≤ V _{CC} < 4.0 V	0	–	0.45 V _{CC}	V
					1.8 V ≤ V _{CC} < 2.7 V	0	–	0.35 V _{CC}	V
I _{OH} (sum)	Peak sum output “H” current	Sum of all pins I _{OH} (peak)			–	–	–160	mA	
I _{OH} (sum)	Average sum output “H” current	Sum of all pins I _{OH} (avg)			–	–	–80	mA	
I _{OH} (peak)	Peak output “H” current	Port P7_0, P7_1, P8 (2)			–	–	–40	mA	
		Other pins			–	–	–10	mA	
I _{OH} (avg)	Average output “H” current (1)	Port P7_0, P7_1, P8 (2)			–	–	–20	mA	
		Other pins			–	–	–5	mA	
I _{OL} (sum)	Peak sum output “L” current	Sum of all pins I _{OL} (peak)			–	–	160	mA	
I _{OL} (sum)	Average sum output “L” current	Sum of all pins I _{OL} (avg)			–	–	80	mA	
I _{OL} (peak)	Peak output “L” current	Port P7_0, P7_1, P8 (2)			–	–	40	mA	
		Other pins			–	–	10	mA	
I _{OL} (avg)	Average output “L” current (1)	Port P7_0, P7_1, P8 (2)			–	–	20	mA	
		Other pins			–	–	5	mA	
f(XIN)	XIN clock input oscillation frequency				2.7 V ≤ V _{CC} ≤ 5.5 V	2	–	20	MHz
					1.8 V ≤ V _{CC} < 2.7 V	2	–	8	MHz
f(XCIN)	XCIN oscillation frequency				1.8 V ≤ V _{CC} ≤ 5.5 V	–	32.768	–	kHz
					XCIN external clock input frequency				1.8 V ≤ V _{CC} ≤ 5.5 V
fOCO20M	When used as the count source for timer RC (3)				2.7 V ≤ V _{CC} ≤ 5.5 V	18.432	–	20	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ V _{CC} ≤ 5.5 V	-	-	20	MHz
					1.8 V ≤ V _{CC} < 2.7 V	-	-	8	MHz
–	System clock frequency				2.7 V ≤ V _{CC} ≤ 5.5 V	-	-	20	MHz
					1.8 V ≤ V _{CC} < 2.7 V	-	-	8	MHz
f(BCLK)	CPU clock frequency				2.7 V ≤ V _{CC} ≤ 5.5 V	0	-	20	MHz
					1.8 V ≤ V _{CC} < 2.7 V	0	-	8	MHz

Notes:

1. The average output current indicates the average value of current measured during 100 ms.
2. This applies when the drive capacity of the output transistor is set to High by registers P7DRR and P8DRR. When the drive capacity is set to Low, the value of any other pin applies.
3. fOCO20M can be used as the count source for timer RC in the range of V_{CC} = 2.7 V to 5.5V.

Table 5.34 Gain Amplifier Characteristics
(VSS = 0 V and Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
VGAIN	Gain amplifier operating range		0.4	–	AVCC – 1.0	V
φAD	A/D conversion clock		1	–	5	MHz

Table 5.35 Comparator B Characteristics
(VCC = 1.8 to 5.5 V and Topr = –20 to 85°C (N version)/–40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
Vref	IVREF1, IVREF3 input reference voltage		0	–	VCC – 1.4	V
Vi	IVCMP1, IVCMP3 input voltage		–0.3	–	VCC + 0.3	V
–	Offset		–	5	100	mV
td	Comparator output delay time ⁽¹⁾	Vi = Vref ± 100 mV	–	–	1	μs
ICMP	Comparator operating current	VCC = 5.0 V	–	12	–	μA

Note:

1. When the digital filter is disabled.

Table 5.36 Flash Memory (Program ROM) Characteristics
(VCC = 1.8 to 5.5 V and Topr = 0 to 60°C, unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽¹⁾		10,000 ⁽²⁾	–	–	times
–	Byte program time		–	80	–	μs
–	Block erase time	Internal ROM Capacity: 16 KB, 32 KB, 48 KB, 64 KB	–	0.12	–	s
		Internal ROM Capacity: 96 KB, 128 KB	–	0.2	–	s
td(SR-SUS)	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	μs
td(CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	μs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time ⁽⁶⁾	Ambient temperature = 85°C	10	–	–	year

Notes:

1. Definition of programming/erasure endurance
The programming and erasure endurance is defined on a per-block basis.
If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.42 High-speed On-Chip Oscillator Circuit Characteristics
($V_{CC} = 1.8$ to 5.5 V and $T_{opr} = -20$ to 85°C (N version)/ -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	$V_{CC} = 1.8$ V to 5.5 V $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	19.2	20	20.8	MHz
		$V_{CC} = 1.8$ V to 5.5 V $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	19.0	20	21.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register ⁽¹⁾	$V_{CC} = 1.8$ V to 5.5 V $-20^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	17.694	18.432	19.169	MHz
		$V_{CC} = 1.8$ V to 5.5 V $-40^{\circ}\text{C} \leq T_{opr} \leq 85^{\circ}\text{C}$	17.510	18.432	19.353	MHz
—	Oscillation stability time		—	5	30	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0$ V, $T_{opr} = 25^{\circ}\text{C}$	—	530	—	μA

Note:

1. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.43 Low-speed On-Chip Oscillator Circuit Characteristics
($V_{CC} = 1.8$ to 5.5 V and $T_{opr} = -20$ to 85°C (N version)/ -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time		—	—	35	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0$ V, $T_{opr} = 25^{\circ}\text{C}$	—	2	—	μA
fOCO-WDT	Low-speed on-chip oscillator frequency for the watchdog timer		60	125	250	kHz
—	Oscillation stability time		—	—	35	μs
—	Self power consumption at oscillation	$V_{CC} = 5.0$ V, $T_{opr} = 25^{\circ}\text{C}$	—	2	—	μA

Table 5.44 Power Supply Circuit Characteristics
($V_{CC} = 1.8$ to 5.5 V, $V_{SS} = 0$ V, and $T_{opr} = 25^{\circ}\text{C}$, unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _d (P-R)	Time for internal power supply stabilization during power-on ⁽¹⁾		—	—	2000	μs

Note:

1. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.51 DC Characteristics (5) [$1.8\text{ V} \leq V_{CC} < 2.7\text{ V}$]
($T_{opr} = -20\text{ to }85^{\circ}\text{C}$ (N version)/ $-40\text{ to }85^{\circ}\text{C}$ (D version), unless otherwise specified.)

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
VoH	Output “H” voltage		Port P7_0, P7_1, P8 (1)	IoH = −2 mA	Vcc − 0.5	−	Vcc	V
			Other pins	IoH = −1 mA	Vcc − 0.5	−	Vcc	V
VoL	Output “L” voltage		Port P7_0, P7_1, P8 (1)	IoL = 2 mA	−	−	0.5	V
			Other pins	IoL = 1 mA	−	−	0.5	V
VT+-VT-	Hysteresis	INT0, INT1, INT2, INT3, INT4, INT5, INT6, INT7, KI0, KI1, KI2, KI3, KI4, KI5, KI6, KI7, TRCIOA, TRCIOB, TRCIOA, TRCIOB, TRCIOA, TRCIOB, TRJ0IO, TRJ1IO, TRJ2IO, TRCTRG, TRCCLK, ADTRG, RXD0, RXD2, CLK0, CLK2, SSI, SCL, SDA, SSO			0.05	0.4	−	V
		RESET, WKUP0			0.1	0.8	−	V
IIH	Input “H” current		VI = 1.8 V, Vcc = 1.8 V		−	−	4.0	μA
IIL	Input “L” current		VI = 0 V, Vcc = 1.8 V		−	−	−4.0	μA
RPULLUP	Pull-up resistance		VI = 0 V, Vcc = 1.8 V		85	220	500	kΩ
RfXIN	Feedback resistance	XIN			−	2.0	−	MΩ
RfXCIN	Feedback resistance	XCIN			−	14	−	MΩ
VRAM	RAM hold voltage		During stop mode		1.8	−	−	V

Note:

1. This applies when the drive capacity of the output transistor is set to High by registers P7DPR and P8DPR. When the drive capacity is set to Low, the value of any other pin applies.

